

NCE P-Channel Enhancement Mode Power MOSFET



The NCE02P20K uses advanced trench technology and design to provide excellent $R_{\text{DS}(\text{ON})}$ with low gate charge. It can be used in a wide variety of applications.

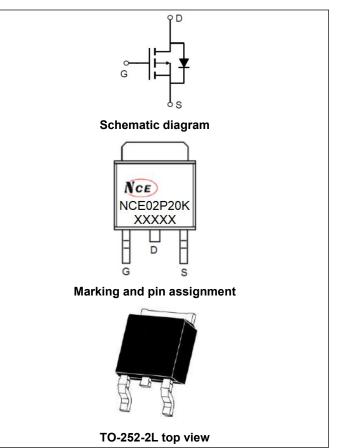
General Features

- V_{DS} =-200V,I_D =-20A
 R_{DS(ON)} <200mΩ @ V_{GS}=-10V (Typ:183mΩ)
 R_{DS(ON)} <240mΩ @ V_{GS}=-4.5V (Typ:188mΩ)
- Super high dense cell design
- Advanced trench process technology
- Reliable and rugged
- High density cell design for ultra low On-Resistance

Application

• Portable equipment and battery powered systems

100% UIS TESTED! 100% ΔVds TESTED!



Package Marking and Ordering Information

	<u> </u>				
Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE02P20K	NCE02P20K	TO-252-2L	-	-	-

Absolute Maximum Ratings (Tc=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	Vds	-200	V	
Gate-Source Voltage	Vgs	±20	V	
Drain Current-Continuous	Ι _D	-20	А	
Drain Current-Continuous(Tc=100℃)	l₀(100°C)	-14.1	A	
Pulsed Drain Current	I _{DM}	-80	A	
Maximum Power Dissipation	PD	180	W	
Single pulse avalanche energy (Note 5)	Eas	282	mJ	
Derating factor		1.2	W/℃	
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C	

Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	R _{θJC}	0.83	°C/W
Thermal Resistance, Junction-to-Ambient (Note 4)	R _{0JA}	50	°C /W



Electrical Characteristics (T_c=25 $^{\circ}$ C unless otherwise noted)

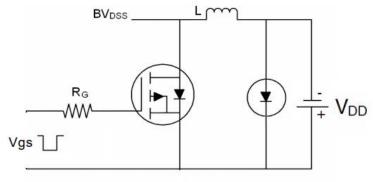
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250µA	-200	-	-	V
Zero Gate Voltage Drain Current	IDSS	V _{DS} =-200V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =-250µA	-1.2	-1.8	-2.5	V
	R _{ds(on)}	V _{GS} =-10V, I _D =-15A	-	183	200	mΩ
Drain-Source On-State Resistance		V _{GS} =-4.5V, I _D =-15A	-	188	220	mΩ
Forward Transconductance	g fs	V _{DS} =-10V,I _D =-20A	-	50	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	Clss		-	6596	-	pF
Output Capacitance	Coss		-	82	-	pF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	59	-	pF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	 V _{DD} =-100V,I _D =-20A V _{GS} =-10V,R _{GEN} =5Ω	-	17	-	nS
Turn-on Rise Time	tr		-	80	-	nS
Turn-Off Delay Time	t _{d(off)}		-	45	-	nS
Turn-Off Fall Time	t _f		-	65	-	nS
Total Gate Charge	Qg	- V _{DS} =-100V,I _D =-20A,	-	122	-	nC
Gate-Source Charge	Qgs		-	19	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =-10V	-	22	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-20A	-	-	-1.2	V
Diode Forward Current (Note 2)	ls	-	-	-	-20	A
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF =-20A	-	90	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/ μ s ^(Note3)	-	145	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD				

Notes:

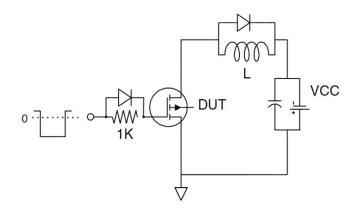
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. The value of R_{BJA} is measured with the device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^{\circ}$ C. The value in any given application depends on the user's specific board design, and the maximum temperature of 150° C may be used if the PCB allows it.
- Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
 Guaranteed by design, not subject to production
- **5.** EAS condition: $Tj=25^{\circ}C$, V_{DD}=-50V, V_G=-10V, L=0.5mH, Rg=25 Ω



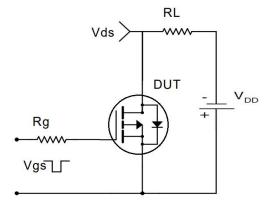
Test Circuit 1) E_{AS} test Circuit



2) Gate charge test Circuit

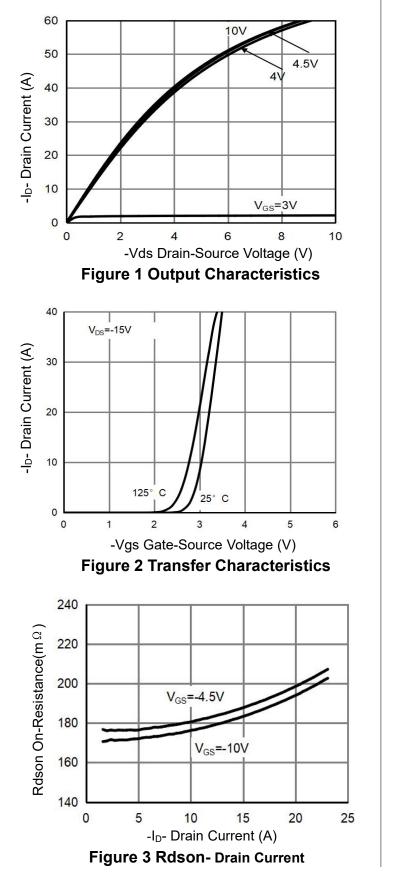


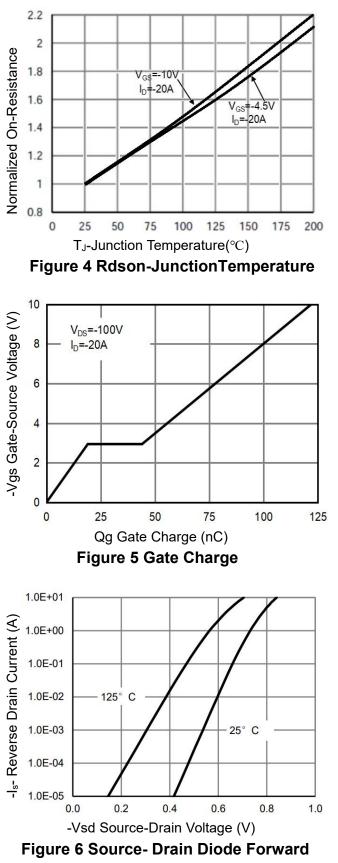
3) Switch Time Test Circuit





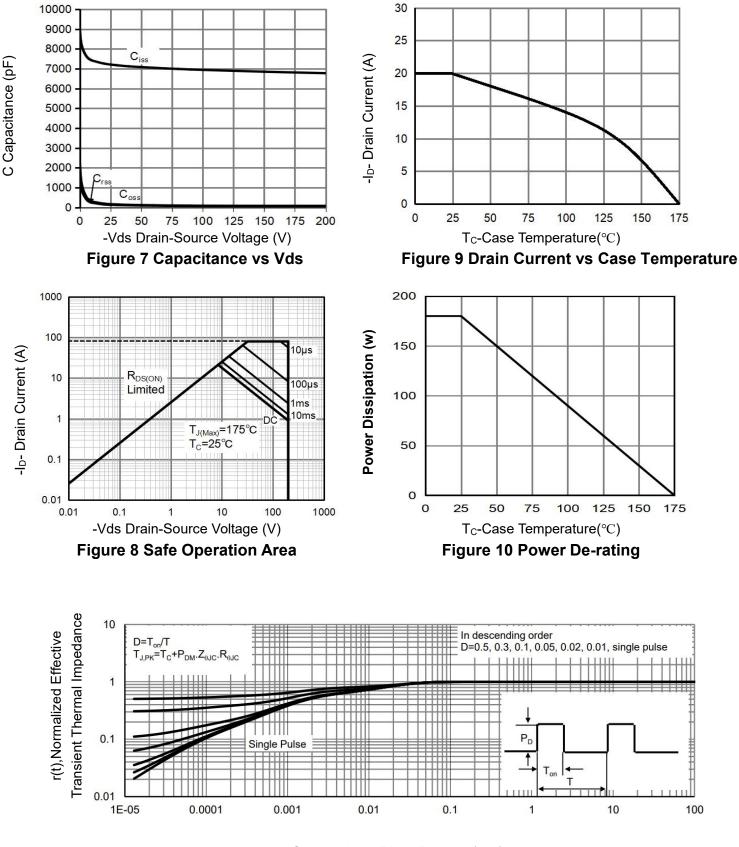
Typical Electrical and Thermal Characteristics (Curves)







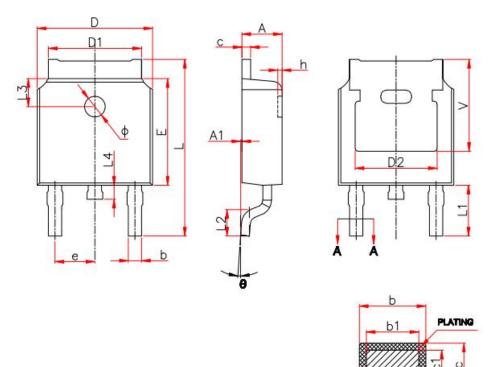
http://www.ncepower.com



Square Wave Pluse Duration(sec) Figure 11 Normalized Maximum Transient Thermal Impedance



TO-252 Package Information



BASE METAL

SECTION A-A

Millimeters Symbol Min. Max. 2.40 2.20 A 0.13 A1 0.00 0.66 0.86 b b1 0.73 0.79 С 0.46 0.58 c1 0.50 0.52 6.50 6.70 D 5.10 5.46 D1 D2 4.83 REF. E 6.00 6.20 2.19 2.39 е 9.80 10.40 L 2.90 REF. L1 1.70 L2 1.40 L3 1.60 REF. L4 0.60 1.00 Φ 1.10 1.30 θ 0° 8° h 0.00 0.30 5.35 REF. V



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